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DIALOG(R) File 351:Derwent WPI

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High purity ammonium fluoride prodn. - by using organic high molecular membrane

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Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
JP 61006121	A	19860111	JP 84123421	A	19840614	198608 B

Priority Applications (No Type Date): JP 84123421 A 19840614

Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
JP 61006121	A		3		

Abstract (Basic): JP 61006121 A

Ammonium fluoride is produced by reacting ammonia with high purity hydrogen fluoride. In the process, ammonia is purified by permeating through organic high molecular membrane to remove impurity. The impurity consists of the cpd. of which element has atomic number 11-83.

Pref. the reaction is carried out at temp. of -10 deg.C - 50 deg.C (pref. 10-40 deg.C), pressure 1-15 kg/sq.cm (pref. 2-10 kg/sq.cm), and water-free atmos. Organic high molecular membrane is a simple complex of polyvinyl trimethyl silane, polycarbonate, cellulose acetate, polyacrylonitrile, etc. Element of atomic number 11-83 is Na, Al, P, Ca, K, Cr, Fe, Ni, Cu, etc.

USE/ADVANTAGE - Ammonium fluoride is used as etching agent of semiconductor or additive of magnetic iron oxide for magnetic tape. With this device, high purity ammonium fluoride or acid ammonium fluoride can be obtd. economically. The obtd. prod. contains impurity below 50 ppm. (3pp Dwg.No.0/0)

Derwent Class: A88; E35; L03

International Patent Class (Additional): C01C-001/16

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1 PN=JP 61151002

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